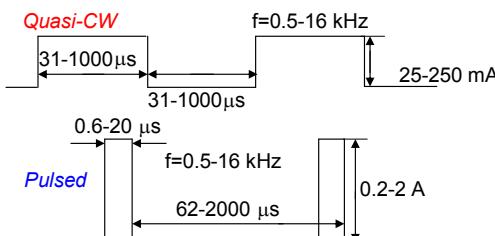
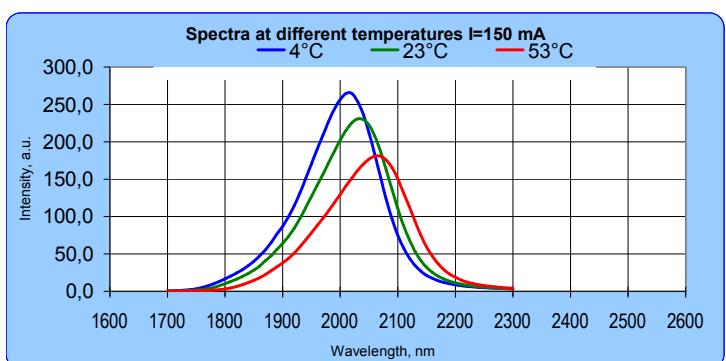
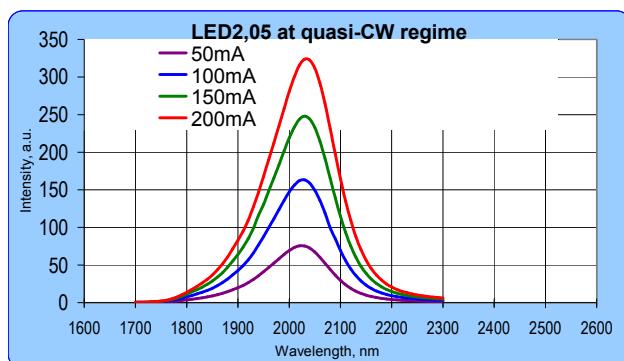




Light Emitting Diodes with central wavelength 2,05  $\mu\text{m}$  series are based on heterostructures grown on GaSb substrates by LPE. Solid solutions GaInAsSb are used in the active layer. Wide band gap solid solutions AlGaAsSb with Al content 64% are used for good electron confinement.

Parameters	Units	Conditions	Ratings		
			Min	Typ	Max
Peak emission wavelength	$\mu\text{m}$	T=300 K	2,02	2,05	2,07
FWHM of the emission band	nm	150 mA CW	150	200	250
Quasi-CW Optical Power	mW	200 mA qCW	0,8	1	1,2
Pulsed Optical Power	mW	1 A	20	25	30
Switching Time	ns	T=300 K	10	20	30
Operating Temperature Range, $^{\circ}\text{C}$			-240° ÷ +50°		
Emitting Area, $\mu\text{m}$			300x300		
Soldering temperature			260 $^{\circ}\text{C}$		
Package					
SMD type package 3×3 mm based on high thermal conductivity ceramics			MID IR LED-SMD3		
SMD type package 5×5 mm based on high thermal conductivity ceramics			MID IR LED-SMD5		
SMD type package 5×5 mm based on high thermal conductivity ceramics with microreflector			<b>MID IR LED-SMD5R</b>		



Maximum current is 220 mA at quasi-CW  
 Maximum pulsed current is 1 A (duration 500 ns, repetition rate 2 kHz)  
 Optimal operating current is 150-200 mA at quasi-CW.

